

## N-Channel Enhancement Mode MOSFET

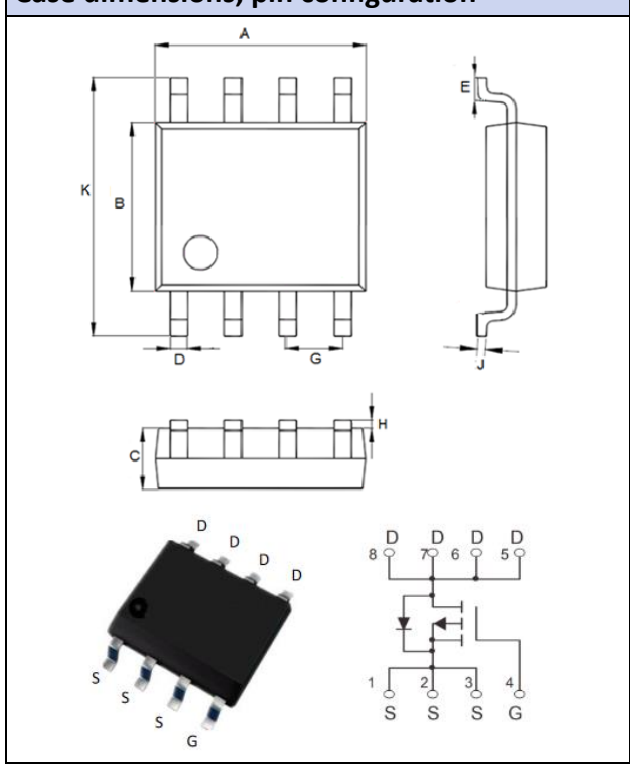
Primary characteristics			
Symbol	Parameter	Value	Unit
$I_D$	Continuous drain current	5.0	A
$V_{DS}$	Drain source voltage	30	V
$R_{DS(on)}$	Static drain-source on-resistance	90	mΩ MAX

### Features

- **SOP-8** case for easy automatic insertion
- Pb-free and **RoHS** compliant
- Trench power MV MOSFET technology
- Excellent package for good heat dissipation

### Applications

- DC-DC converters
- Power management functions

Case dimensions, pin configuration										
 <p>The diagram shows the SOP-8 package with dimensions A, B, C, D, E, G, H, J, K. It includes a top view, a side view, a perspective view, and a pin configuration diagram. The pin configuration diagram shows pins 1-4 as Source (S) and pins 5-8 as Drain (D).</p>										
<b>SOP-8</b>										
Unit		A	B	C	D	E	G	H	J	K
mm	MIN	4.8	3.8	1.3	0.3	0.4	1.17	0.1	0.1	5.8
	MAX	5.2	4.2	1.5	0.5	1.0	1.37	0.3	0.3	6.2

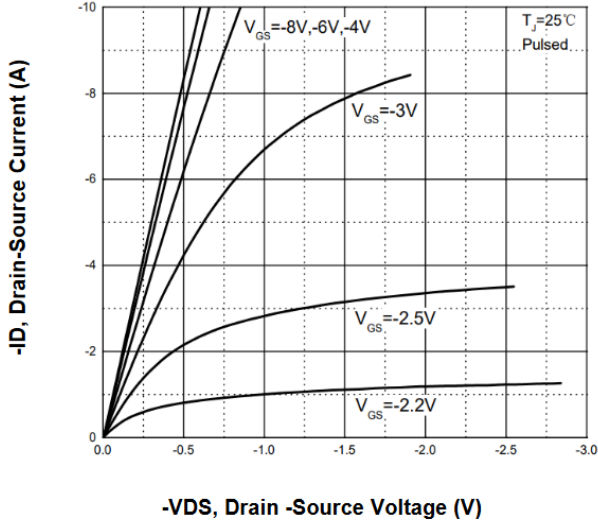
### Maximum ratings ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	30	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Diode continuous forward current ( $T_C=25^\circ\text{C}$ )	$I_S$	5.0	A
Continuous drain current ( $V_{GS}=10\text{V}$ , $T_C=25^\circ\text{C}$ )	$I_D$	5.0	A
Pulsed drain current ( $T_C=25^\circ\text{C}$ )	$I_{DM}$	20	A
Power Dissipation	$P_D$	2.5	W
Maximum junction temperature	$T_J$	150	$^\circ\text{C}$
Storage temperature range	$T_{STG}$	-50 ~ 155	$^\circ\text{C}$
Thermal resistance junction-ambient (1 inch <sup>2</sup> pad of 2-oz copper, max.)	$R_{\theta JA}$	50	$^\circ\text{C/W}$

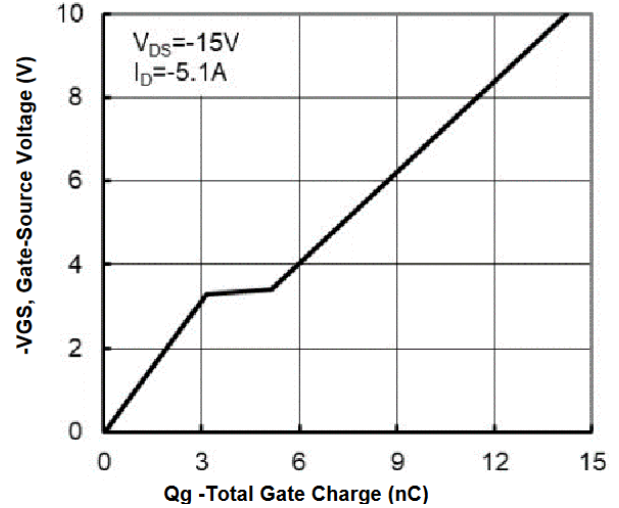
Electrical characteristics (T <sub>J</sub> = 25°C)						
Characteristic	Test condition	Symbol	Value			Unit
			Min.	Typ.	Max.	
Drain-source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	V <sub>(BR)DSS</sub>	30	-	-	V
Zero gate voltage drain current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	I <sub>DSS</sub>	-	-	1.0	μA
Gate body leakage current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	I <sub>GSS</sub>	-	-	±100	nA
Gate threshold voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	V <sub>GS(TH)</sub>	1.0	1.5	2.5	V
Drain-source on-state resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4.6A	R <sub>DS(ON)</sub>	-	45	60	mΩ
	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.1A		-	60	90	
Dynamic electrical characteristics (T <sub>J</sub> = 25°C)						
Characteristic	Test condition	Symbol	Value			Unit
			Min.	Typ.	Max.	
Input capacitance	V <sub>DS</sub> =15V V <sub>GS</sub> =0V f=1.0MHz	C <sub>ISS</sub>	-	770	-	pF
Output capacitance		C <sub>OSS</sub>	-	440	-	
Reverse transfer capacitance		C <sub>RSS</sub>	-	123	-	
Turn ON delay time	V <sub>DS</sub> =15V V <sub>GS</sub> =10V R <sub>G</sub> =3.0Ω I <sub>D</sub> =1.0A	t <sub>d(ON)</sub>	-	9.0	-	ns
Turn ON rise time		t <sub>r</sub>	-	16	-	
Turn OFF delay time		t <sub>d(OFF)</sub>	-	77	-	
Turn OFF fall time		t <sub>f</sub>	-	40	-	
Switching characteristics						
Characteristic	Test condition	Symbol	Value			Unit
			Min.	Typ.	Max.	
Total gate-charge	V <sub>DS</sub> =15V V <sub>GS</sub> =10V I <sub>D</sub> =4.2A	Q <sub>G</sub>	-	30	-	nC
Gate to source charge		Q <sub>GS</sub>	-	2.7	-	
Gate to drain (Miller) charge		Q <sub>GD</sub>	-	6.9	-	
Source-drain diode characteristics						
Characteristic	Test condition	Symbol	Value			Unit
			Min.	Typ.	Max.	
Diode forward voltage	I <sub>SD</sub> =5.0A, T <sub>J</sub> =25°C	V <sub>SD</sub>	-	-	1.2	V

Typical characteristics

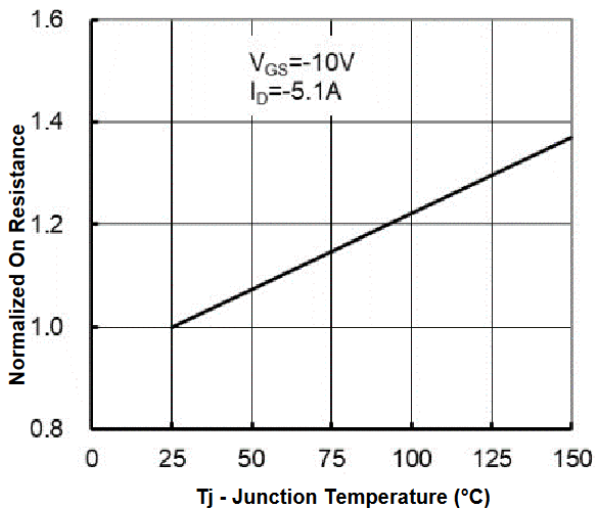
Typical output characteristics



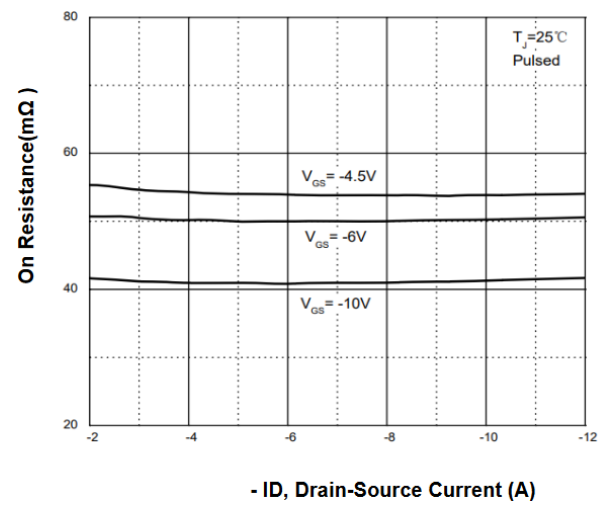
Typical gate charge vs gate-source voltage



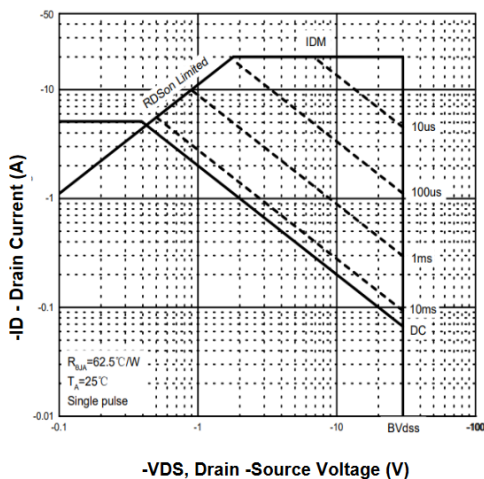
Normalized ON-resistance vs. temperature



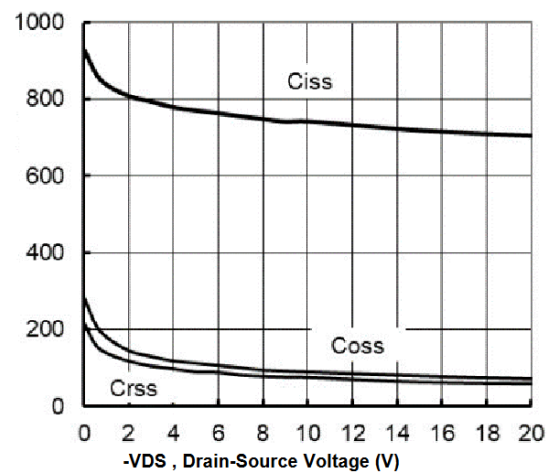
ON-resistance vs. drain-source current

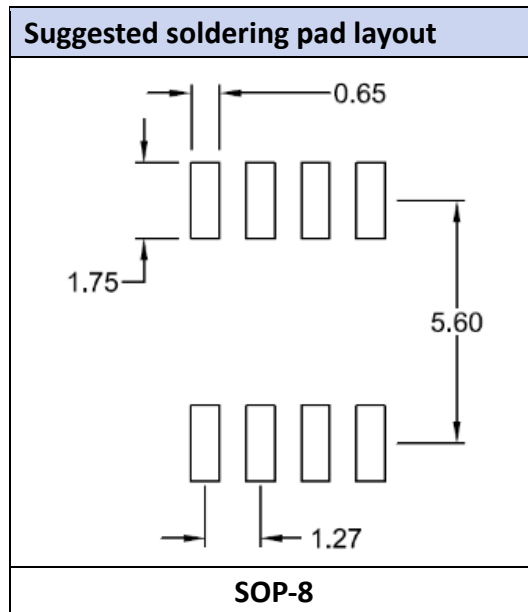


Maximum safe operating area



Typical capacitance vs. drain-source voltage





Ordering information				
Part Number	Marking	Package	Shipping Quantity	Dimensions
AKS9435A	9435A	SOP-8	3000 pcs / tape & reel	---

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